S-8264A/B/C Series

BATTERY PROTECTION IC FOR 2-SERIAL TO 4-SERIAL-CELL PACK (SECONDARY PROTECTION)

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SII •

Rev.4.0 00

The S-8264A/B/C Series is used for secondary protection of lithium-ion rechargeable batteries, and incorporates a high-accuracy voltage detection circuit and a delay circuit. Short-circuits between cells accommodate series connection of two to four cells.

Features

- (1) High-accuracy voltage detection circuit for each cell
 - Overcharge detection voltage n (n = 1 to 4)
 - 4.20 V to 4.80 V (in 50 mV steps) Accuracy : ±25 mV (+25°C), Accuracy : ±30 mV (-5°C to +55°C)
 Overcharge hysteresis voltage n (n = 1 to 4)
 - –0.52 ±0.21 V, –0.39 ±0.16 V, –0.26 ±0.11 V, –0.13 ±0.06 V, None
- (2) Delay times for overcharge detection can be set by an internal circuit only (external capacitors are unnecessary)
- (3) Output control function via CTL pin (CTL pin is pulled down internally) (S-8264A Series) Output control function via CTL pin (CTL pin is pulled up internally) (S-8264C Series)
- (4) Output latch function after overcharge detection (S-8264B Series)
- (5) Output form and logic CMOS output active "H"
- (6) High withstand voltage devices Absolute maximum rating : 26 V
- (7) Wide operating voltage range 3.6 V to 24 V
- (8) Wide operating temperature range -40° C to $+85^{\circ}$ C
- (9) Low current consumption
 - At 3.5 V for each cell 5.0 μA max. (+25°C)
 - At 2.3 V for each cell
 4.0 μA max. (+25°C)
- (10) Lead-free, Sn 100%, halogen-free*1
- *1. Refer to "
 Product Name Structure" for details.

Application

• Lithium-ion rechargeable battery packs (for secondary protection)

Packages

- SNT-8A
- 8-Pin TSSOP

Block Diagrams

(1) S-8264A Series



Remark The diodes in the figure are parasitic diodes.



(2) S-8264B Series



Remark The diodes in the figure are parasitic diodes.



(3) S-8264C Series



Remark The diodes in the figure are parasitic diodes.

Figure 3

Product Name Structure



*1. Refer to the tape specifications at the end of this book.

*2. Refer to "3. Product Name List".

2. Package

De	okago Namo		Drawing Code						
Package Name Package Tape				Reel	Land				
SNT-8A		PH008-A-P-SD	PH008-A-C-SD	PH008-A-R-SD	PH008-A-L-SD				
	Environmental code = G	FT008-A-P-SD	FT008-E-C-SD	FT008-E-R-SD					
0-FIII 1330F	Environmental code = U	FT008-A-P-SD	FT008-E-C-SD	FT008-E-R-S1					

3. Product Name List

(1) S-8264A Series

$ \begin{array}{c c c c c c c c c c c c c c c c c c c $					
S-8264AAA-I8T1x $4.45 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $4.0 \pm 0.8 \text{ s}$ CMOS output active "H"S-8264AAB-I8T1x $4.35 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $4.0 \pm 0.8 \text{ s}$ CMOS output active "H"S-8264AAC-I8T1x $4.50 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $4.0 \pm 0.8 \text{ s}$ CMOS output active "H"S-8264AAC-I8T1x $4.50 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $4.0 \pm 0.8 \text{ s}$ CMOS output active "H"S-8264AAD-I8T1x $4.35 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $2.0 \pm 0.4 \text{ s}$ CMOS output active "H"S-8264AAE-I8T1x $4.30 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $4.0 \pm 0.8 \text{ s}$ CMOS output active "H"S-8264AAF-I8T1x $4.45 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $2.0 \pm 0.4 \text{ s}$ CMOS output active "H"S-8264AAG-I8T1x $4.45 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $2.0 \pm 0.4 \text{ s}$ CMOS output active "H"S-8264AAG-I8T1x $4.40 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $2.0 \pm 0.4 \text{ s}$ CMOS output active "H"S-8264AAH-I8T1x $4.40 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $2.0 \pm 0.4 \text{ s}$ CMOS output active "H"S-8264AAI-I8T1x $4.40 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $2.0 \pm 0.4 \text{ s}$ CMOS output active "H"S-8264AAJ-I8T1x $4.40 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $2.0 \pm 0.4 \text{ s}$ CMOS output active "H"S-8264AAJ-I8T1x $4.45 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $2.0 \pm 0.4 \text{ s}$ CMOS output active "H"S-8264AAJ-I8T1x $4.45 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ $5.65 \pm 1.15 \text{ s}$ CMOS output active "H"S-8264AAK-I8T1x $4.35 \pm 0.025 \vee$ $-0.39 \pm 0.16 \vee$ </td <td>Product Name</td> <td>Overcharge Detection Voltage [V_{CU}]</td> <td>Overcharge Hysteresis Voltage [V_{HC}]</td> <td>Overcharge Detection Delay Time [t_{cu}]</td> <td>Output Form</td>	Product Name	Overcharge Detection Voltage [V _{CU}]	Overcharge Hysteresis Voltage [V _{HC}]	Overcharge Detection Delay Time [t _{cu}]	Output Form
S-8264AAB-I8T1x 4.35 ±0.025 V -0.39 ±0.16 V 4.0 ±0.8 s CMOS output active "H" S-8264AAC-I8T1x 4.50 ±0.025 V -0.39 ±0.16 V 4.0 ±0.8 s CMOS output active "H" S-8264AAD-I8T1x 4.35 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAE-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAE-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAF-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAF-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAG-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAH-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAI-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAJ-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAJ-I8T1x	S-8264AAA-I8T1x	4.45 ±0.025 V	-0.39 ±0.16 V	4.0 ±0.8 s	CMOS output active "H"
S-8264AAC-I8T1x 4.50 ±0.025 V -0.39 ±0.16 V 4.0 ±0.8 s CMOS output active "H" S-8264AAD-I8T1x 4.35 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAE-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 4.0 ±0.8 s CMOS output active "H" S-8264AAE-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 4.0 ±0.8 s CMOS output active "H" S-8264AAF-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAG-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAH-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAH-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 4.0 ±0.8 s CMOS output active "H" S-8264AAI-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAJ-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAJ-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H" S-8264AAK-I8T1x <td>S-8264AAB-I8T1x</td> <td>4.35 ±0.025 V</td> <td>–0.39 ±0.16 V</td> <td>4.0 ±0.8 s</td> <td>CMOS output active "H"</td>	S-8264AAB-I8T1x	4.35 ±0.025 V	–0.39 ±0.16 V	4.0 ±0.8 s	CMOS output active "H"
S-8264AAD-I8T1x 4.35 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAE-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 4.0 ±0.8 s CMOS output active "H" S-8264AAF-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAF-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAG-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAH-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAI-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAI-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAJ-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAJ-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H" S-8264AAK-I8T1x 4.35 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H"	S-8264AAC-I8T1x	4.50 ±0.025 V	–0.39 ±0.16 V	4.0 ±0.8 s	CMOS output active "H"
S-8264AAE-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 4.0 ±0.8 s CMOS output active "H" S-8264AAF-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAG-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAG-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAH-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAI-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAI-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAJ-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAJ-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H" S-8264AAK-I8T1x 4.35 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H"	S-8264AAD-I8T1x	4.35 ±0.025 V	–0.39 ±0.16 V	2.0 ±0.4 s	CMOS output active "H"
S-8264AAF-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAG-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAH-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 4.0 ±0.8 s CMOS output active "H" S-8264AAH-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 4.0 ±0.8 s CMOS output active "H" S-8264AAI-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAJ-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAJ-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H" S-8264AAK-I8T1x 4.35 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H"	S-8264AAE-I8T1x	4.30 ±0.025 V	-0.39 ±0.16 V	4.0 ±0.8 s	CMOS output active "H"
S-8264AAG-I8T1x 4.30 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAH-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 4.0 ±0.8 s CMOS output active "H" S-8264AAI-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAI-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAJ-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H" S-8264AAK-I8T1x 4.35 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H"	S-8264AAF-I8T1x	4.45 ±0.025 V	–0.39 ±0.16 V	2.0 ±0.4 s	CMOS output active "H"
S-8264AAH-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 4.0 ±0.8 s CMOS output active "H" S-8264AAI-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAJ-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H" S-8264AAK-I8T1x 4.35 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H"	S-8264AAG-I8T1x	4.30 ±0.025 V	–0.39 ±0.16 V	2.0 ±0.4 s	CMOS output active "H"
S-8264AAI-I8T1x 4.40 ±0.025 V -0.39 ±0.16 V 2.0 ±0.4 s CMOS output active "H" S-8264AAJ-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H" S-8264AAK-I8T1x 4.35 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H"	S-8264AAH-I8T1x	4.40 ±0.025 V	–0.39 ±0.16 V	4.0 ±0.8 s	CMOS output active "H"
S-8264AAJ-I8T1x 4.45 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H" S-8264AAK-I8T1x 4.35 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H"	S-8264AAI-I8T1x	4.40 ±0.025 V	–0.39 ±0.16 V	2.0 ±0.4 s	CMOS output active "H"
S-8264AAK-I8T1x 4.35 ±0.025 V -0.39 ±0.16 V 5.65 ±1.15 s CMOS output active "H"	S-8264AAJ-I8T1x	4.45 ±0.025 V	–0.39 ±0.16 V	$5.65 \pm 1.15 s$	CMOS output active "H"
	S-8264AAK-I8T1x	$4.35 \pm \! 0.025 \ V$	–0.39 ±0.16 V	5.65 ±1.15 s	CMOS output active "H"

Table 1 SNT-8A

Table 2 8-Pin TSSOP

Product Name	Overcharge Detection Voltage [V _{CU}]	Overcharge Hysteresis Voltage [V _{HC}]	Overcharge Detection Delay Time [t _{cu}]	Output Form
S-8264AAA-T8T1x	4.45 ±0.025 V	–0.39 ±0.16 V	4.0 ±0.8 s	CMOS output active "H"
S-8264AAB-T8T1x	4.35 ±0.025 V	–0.39 ±0.16 V	4.0 ±0.8 s	CMOS output active "H"

(2) S-8264B Series

Table 3 SNT-8A

Product Name	Overcharge Detection Voltage [V _{CU}]	Overcharge Hysteresis Voltage [V _{HC}]	Overcharge Detection Delay Time [t _{cu}]	Output Form
S-8264BAA-I8T1x	4.45 ±0.025 V	–0.39 ±0.16 V	4.0 ±0.8 s	CMOS output active "H"
S-8264BAB-I8T1x	4.35 ±0.025 V	–0.39 ±0.16 V	4.0 ±0.8 s	CMOS output active "H"

(3) S-8264C Series

Table 4 SNT-8A

Product Name	Overcharge Detection Voltage [V _{CU}]	Overcharge Hysteresis Voltage [V _{HC}]	Overcharge Detection Delay Time [t _{CU}]	Output Form
S-8264CAA-I8T1U	4.45 ±0.025 V	–0.39 ±0.16 V	2.0 ±0.4 s	CMOS output active "H"
S-8264CAB-I8T1U	4.22 ±0.025 V	-0.26 ±0.11 V	2.0 ±0.4 s	CMOS output active "H"

Remark 1. Please contact our sales department for the products with detection voltage value other than those specified above.

- 2. x: G or U
- 3. Please select products of environmental code = U for Sn 100%, halogen-free products.

Pin Configurations

SNT-8A Top viewPin No.SymbolDescriptionVDD1VDDPositive power input pin2SENSEPositive voltage connection pin of battery 13VC1Negative voltage connection pin of battery 24VC2Negative voltage connection pin of battery 3VC136VC136VC2VC3Negative voltage connection pin of battery 46VSSNegative voltage connection pin of battery 47CTLCO output control pin (S-8264A/C Series) Overcharge detection latch reset pin (S-8264B Series)8COFET gate connection pin for charge
SNT-8A Top view 1 VDD Positive power input pin VDD 1 8 CO SENSE 2 7 CTL VC1 3 VC1 Negative voltage connection pin of battery 1 VC1 0 1 CO VC1 0 1 0 VC1 0 0 CTL VC2 0 0 CTL VC2 0 0 CTL VC3 0 0 0 VSS 0 0
SNT-8A Top view 3 VC1 Negative voltage connection pin of battery 1 VDD 0 8 CO Positive voltage connection pin of battery 2 VC1 0 1 0 0 1 Positive voltage connection pin of battery 2 VDD 1 0 1 0 1 0 1 Positive voltage connection pin of battery 2 VDD 1 0 1 0 1 Positive voltage connection pin of battery 2 VC1 1 0 1 0 1 Positive voltage connection pin of battery 2 VC1 3 6 1 VC2 Negative voltage connection pin of battery 3 VC2 4 VC3 Positive voltage connection pin of battery 4 Positive voltage connection pin of battery 4 7 CTL Negative voltage connection pin of battery 4 Positive voltage connection pin of battery 4 7 CTL CO output control pin (S-8264A/C Series) Overcharge detection latch reset pin (S-8264B Series) 8 CO FET gate connection pin for charge Positive connection pin for charge
Top viewVDD181COSENSE271CTLVC1361VC2VC1361VC3VC24VC2Negative voltage connection pin of battery 2 Positive voltage connection pin of battery 3VC1361VC24VC2Negative voltage connection pin of battery 3 Positive voltage connection pin of battery 4VC24VC3Negative voltage connection pin of battery 46VSSNegative voltage connection pin of battery 47CTLCO output control pin (S-8264A/C Series) Overcharge detection latch reset pin (S-8264B Series)8COFET gate connection pin for charge
VDD 1 8 1 CO 8 1 CO SENSE 2 7 1 CTL Positive voltage connection pin of battery 3 VC1 3 6 1 VSS Negative voltage connection pin of battery 3 VC2 4 5 VC3 Negative voltage connection pin of battery 3 VC2 4 5 VC3 Negative voltage connection pin of battery 4 6 VSS Negative voltage connection pin of battery 4 7 CTL CO output control pin (S-8264A/C Series) 0vercharge detection latch reset pin (S-8264B Series) 8 CO 8 CO FET gate connection pin for charge
VC1 I 3 6 VSS 5 VC3 Negative voltage connection pin of battery 3 Positive voltage connection pin of battery 4 VC2 I 5 VC3 Negative voltage connection pin of battery 4 6 VSS Negative voltage connection pin of battery 4 7 CTL CO output control pin (S-8264A/C Series) Overcharge detection latch reset pin (S-8264B Series) 8 CO FET gate connection pin for charge
VC2 [[4 5]] VC3 6 VSS Negative power input pin Negative voltage connection pin of battery 4 7 CTL CO output control pin (S-8264A/C Series) Overcharge detection latch reset pin (S-8264B Series) 8 CO FET gate connection pin for charge
7CTLCO output control pin (S-8264A/C Series) Overcharge detection latch reset pin (S-8264B Series)8COFET gate connection pin for charge
8 CO FET gate connection pin for charge
Figure 4 Table 6
Pin No. Symbol Description
1 VDD Positive power input pin
8-Pin TSSOP 2 SENSE Positive voltage connection pin of battery 1
Top view 3 VC1 Negative voltage connection pin of battery 1 Positive voltage connection pin of battery 2
VDD 1 8 CO SENSE 2 7 CTL 4 VC2 Negative voltage connection pin of battery 2 VOL 2 7 CTL 4 VC2 Positive voltage connection pin of battery 3
VC1 II 3 6 II VSS VC2 II 4 5 II VC3 5 VC3 Negative voltage connection pin of battery 3 Positive voltage connection pin of battery 4
6 VSS Negative power input pin Negative voltage connection pin of battery 4
7 CTL CO output control pin (S-8264A/C Series) Overcharge detection latch reset pin (S-8264B Series)

Figure 5

Absolute Maximum Ratings

Table 7

			(la=	25°C unless otherwise sp	pecified)
	Item	Symbol	Applied Pins	Rating	Unit
Input voltage betw	een VDD and VSS	V _{DS}	VDD	$V_{\text{SS}} - 0.3$ to $V_{\text{SS}} + 26$	V
Input pin voltage		VIN	SENSE, VC1, VC2, VC3, CTL	$V_{\text{SS}} - 0.3$ to $V_{\text{DD}} + 0.3$	V
CO output pin volta	age	Vco	CO	$V_{\text{SS}} - 0.3$ to $V_{\text{DD}} + 0.3$	V
Dower dissinction	SNT-8A	D		450 ^{*1}	mW
Power dissipation	8-Pin TSSOP	PD	—	700 ^{*1}	mW
Operation ambient	temperature	T _{opr}	<u> </u>	-40 to +85	°C
Storage temperatu	re	T _{stg}		-40 to +125	°C

*1. When mounted on board

[Mounted board]

(1) Board size : 114.3 mm \times 76.2 mm \times t1.6 mm

(2) Name : JEDEC STANDARD51-7

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.



Figure 6 Power Dissipation of Package (When Mounted on Board)

Table 8

Electrical Characteristics

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1. Except Detection Delay Time

					(Ta = 25°	C unless	otherwise	specified)
Item	Symbol	Conditions	Min.	Тур.	Max.	Unit	Test Condition	Test Circuit
DETECTION VOLTAGE								
Overcharge detection voltage n (n = 1, 2, 3, 4)	V _{CUn}	4.20 V to 4.80 V, adjustable, Ta = 25° C	V _{CUn} -0.025	V _{CUn}	V _{CUn} +0.025	V	1	1
		4.20 V to 4.80 V, adjustable, Ta = -5° C to $+55^{\circ}$ C ^{*1}	V _{CUn} -0.030	V _{CUn}	V _{CUn} +0.030	V	1	1
Overcharge hysteresis voltage n ² (n = 1, 2, 3, 4)	V _{HCn}	_	V _{HCn} -0.21	-0.52	V _{HCn} +0.21	V	1	1
INPUT VOLTAGE		i	 		,		.	
Operating voltage between VDD and VSS	V _{DSOP}	—	3.6		24	V		
CTL input "H" voltage	V _{CTLH}		V _{DD} ×0.95			V	6	2
CTL input "L" voltage	V _{CTLL}				V _{DD} ×0.4	V	6	2
INPUT CURRENT					•			
Current consumption during operation	I _{OPE}	V1 = V2 = V3 = V4 = 3.5 V	—	2.5	5.0	μA	7	4
Current consumption during overdischarge	I _{OPED}	V1 = V2 = V3 = V4 = 2.3 V		2.0	4.0	μA	7	4
SENSE pin current	I _{SENSE}	V1 = V2 = V3 = V4 = 3.5 V		1.5	3.2	μA	8	5
VC1 pin current	I _{VC1}	V1 = V2 = V3 = V4 = 3.5 V	-0.3	0	0.3	μΑ	8	5
VC2 pin current	I _{VC2}	V1 = V2 = V3 = V4 = 3.5 V	-0.3	0	0.3	μA	8	5
VC3 pin current	I _{VC3}	V1 = V2 = V3 = V4 = 3.5 V	-0.3	0	0.3	μA	8	5
CTL pin "H" current		A/B Series V1 = V2 = V3 = V4 = 3.5 V, V _{CTL} = V _{DD}	1.1	1.5	1.8	μA	8	5
CTL pin "H" current	^I CILH	C Series V1 = V2 = V3 = V4 = 3.5 V V _{CTL} = V _{DD}			0.15	μA	8	5
CTL sin "I" ourrent		A/B Series V1 = V2 = V3 = V4 = 3.5 V, V _{CTL} = 0 V	-0.15	_		μΑ	8	5
CTL pin L current	ICTLL	С Series V1 = V2 = V3 = V4 = 3.5 V Vстц = 0 V	-150	-50	-10	μA	8	5
OUTPUT CURRENT	-	012						
CO pin sink current	I _{COL}	$V_{COP} = V_{SS} + 0.5 V$	0.4			mA	9	6
CO pin source current	I _{COH}	$V_{COP} = V_{DD} - 0.5 V$	20			μA	9	6

*1. Since products are not screened at high and low temperature, the specification for this temperature range is guaranteed by design, not tested in production.

*2. -0.39 ±0.16 V, -0.26 ±0.11 V, -0.13 ±0.06 V, or none, except for -0.52 V hysteresis product circuits. The overcharge release voltage is the total of the overcharge detection voltage (V_{CUn}) and the overcharge hysteresis voltage (V_{HCn}).

2. Detection Delay Time

(1) S-8264AAA, S-8264AAB, S-8264AAC, S-8264AAE, S-8264AAH, S-8264BAA, S-8264BAB

Table 9

					(Ta = 25°C	unless c	otherwise sp	pecified)
Item	Symbol	Conditions	Min.	Тур.	Max.	Unit	Test Condition	Test Circuit
DELAY TIME			-		-			
Overcharge detection delay time	t _{cu}		3.2	4.0	4.8	s	2	1
Overcharge timer reset delay time	t _{TR}		6	12	20	ms	3	1
Overcharge release delay time	t _{CL}		51	64	77	ms	2	1
CTL pin response time	t _{CTL}	—			2.5	ms	4	2
Transition time to Test mode	t _{TST}	$\label{eq:V1} \begin{array}{l} V1 = V2 = V3 = V4 = 3.5 \ V, \\ V_{DD} \geq V_{SENSE} + 8.5 \ V \end{array}$			80	ms	5	3

(2) S-8264AAD, S-8264AAF, S-8264AAG, S-8264AAI, S-8264CAA, S-8264CAB

Table 10

					(Ta = 25°C	unless c	otherwise sp	pecified)
Item	Symbol	Conditions	Min.	Тур.	Max.	Unit	Test Condition	Test Circuit
DELAY TIME								
Overcharge detection delay time	t _{cu}		1.6	2.0	2.4	S	2	1
Overcharge timer reset delay time	t _{TR}		6	12	20	ms	3	1
Overcharge release delay time	t _{CL}		1.6	2.0	3.0	ms	2	1
CTL pin response time	t _{CTL}	_	_	_	2.5	ms	4	2
Transition time to Test mode	t _{TST}			_	80	ms	5	3

(3) S-8264AAJ, S-8264AAK

Table 11

					(Ta = 25°C	unless c	otherwise sp	pecified)
Item	Symbol	Conditions	Min.	Тур.	Max.	Unit	Test Condition	Test Circuit
DELAY TIME								
Overcharge detection delay time	t _{cu}		4.5	5.65	6.8	s	2	1
Overcharge timer reset delay time	t _{TR}		8	17	28	ms	3	1
Overcharge release delay time	t _{CL}		70	88	110	ms	2	1
CTL pin response time	t _{CTL}	_			2.5	ms	4	2
Transition time to Test mode	t _{TST}	$ \begin{array}{l} V1 = V2 = V3 = V4 = 3.5 \ V, \\ V_{DD} \geq V_{SENSE} + 8.5 \ V \end{array} $			80	ms	5	3

Test Circuits

(1) Test Condition 1, Test Circuit 1

Set V1, V2, V3, and V4 to 3.5 V. Overcharge detection voltage 1 (V_{CU1}) is the V1 voltage when CO is "H" after the voltage of V1 has been gradually increased. The overcharge hysteresis voltage (V_{HC1}) is the difference between V1 and V_{CU1} when CO is "L" after the voltage of V1 has been gradually decreased.

Overcharge detection voltage V_{CUn} (n = 2 to 4) and overcharge hysteresis V_{HCn} (n = 2 to 4) can be determined in the same way as when n = 1.

(2) Test Condition 2, Test Circuit 1

Set V1, V2, V3, and V4 to 3.5 V and in a moment of time (within 10 μ s) increase V1 up to 5.0 V. The overcharge detection delay time (t_{CU}) is the period from when V1 reached 5.0 V to when CO becomes "H". After that, in a moment of time (within 10 μ s) decrease V1 down to 3.5 V. The overcharge release delay time (t_{CL}) is the period from when V1 has reached 3.5 V to when CO becomes "L".

(3) Test Condition 3, Test Circuit 1

Set V1, V2, V3, and V4 to 3.5 V and in a moment of time (within 10 μ s) increase V1 up to 5.0 V. This is defined as the first rise. Within t_{CU} – 20 ms after the first rise, in a moment of time (within 10 μ s) decrease V1 down to 3.5 V and then in a moment of time (within 10 μ s) restore up to 5.0 V. This is defined as the second rise. When the period from when V1 was fallen to the second rise is short, CO becomes "H" after t_{CU} has elapsed since the first rise. If the period from when V1 falls to the second rise is gradually made longer, CO becomes "H" when t_{CU} has elapsed since the second rise. The overcharge timer reset delay time (t_{TR}) is the period from V1 fall till the second rise at that time.

(4) Test Condition 4, Test Circuit 2

In the S-8264A/C Series, set V1, V2, V3, and V4 to 3.5 V and V5 to 14 V. The CTL pin response time (t_{CTL}) is the period from when V5 reaches 0 V after V5 is in a moment of time (within 10 μ s) decreased down to 0 V to when CO becomes "H".

In the S-8264B Series, set V1, V2, V3, and V4 to 3.5 V and V5 to 14 V after an overvoltage is detected and CO becomes "H". In a moment of time (within 10 μ s) raise V5 from 0 V to 14 V. The CTL pin response time (t_{CTL}) is the period from when V5 becomes 14 V to when CO becomes "L".

(5) Test Condition 5, Test Circuit 3

After setting V1, V2, V3, and V4 to 3.5 V and V5 to 0 V, in a moment of time (within 10 μ s) increase V5 up to 8.5 V and decrease V5 again down to 0 V. When the period from when V5 was raised to when it has fallen is short, if an overcharge detection operation is performed subsequently, the overcharge detection time is t_{CU}. However, when the period from when V5 is raised to when it is fallen is gradually made longer, the overcharge detection time during the subsequent overcharge detection operation is shorter than t_{CU}. The transition time to test mode (t_{TST}) is the period from when V5 was raised to when it has fallen at that time.

(6) Test Condition 6, Test Circuit 2

Set V1, V2, V3, and V4 to 3.5 V and V5 to 0 V. The CTL input "H" voltage (V_{CTLH}) is the maximum voltage of V5 when CO is "L" after V5 has been gradually increased. Next, set V5 to 14 V. The CTL input "L" voltage (V_{CTLL}) is the minimum voltage of V5 when CO is "H" after V5 has been gradually decreased.

(7) Test Condition 7, Test Circuit 4

The current consumption during operation (I_{OPE}) is the total of the currents that flow in the VDD pin and SENSE pin when V1, V2, V3, and V4 are set to 3.5 V.

The current consumption during overdischarge (I_{OPED}) is the total of the currents that flow in the VDD pin and SENSE pin when V1, V2, V3, and V4 are set to 2.3 V.

(8) Test Condition 8, Test Circuit 5

The SENSE pin current (I_{SENSE}) is 11, the VC1 pin current (I_{VC1}) is 12, the VC2 pin current (I_{VC2}) is 13, the VC3 pin current (I_{VC3}) is 14, and the CTL pin "H" current (I_{CTLH}) is 15 when V1, V2, V3, and V4 are set to 3.5 V, and V5 to 14 V. The CTL pin "L" current (I_{CTLL}) is 15 when V1, V2, V3, and V4 are set to 3.5 V and V5 to 0 V.

(9) Test Condition 9, Test Circuit 6

Set SW1 to OFF and SW2 to ON. The CO pin sink current (I_{COL}) is I2 when V1, V2, V3, and V4 are set to 3.5 V and V6 to 0.5 V.

Set SW1 and SW2 to OFF. Set V1 to V5, set V2, V3, and V4 to 3.0 V, and set V5 to 0.5 V. After t_{CU} has elapsed, set SW1 to ON and SW2 to OFF. I1 is the CO pin source current (I_{COH}).



Test Circuit 1



Test Circuit 3



Test Circuit 5



Test Circuit 2



Test Circuit 4



Test Circuit 6

Figure 7

Operation

Remark Refer to "
Battery Protection IC Connection Example".

1. Overcharge Detection

When the voltage of one of the batteries exceeds the overcharge detection voltage (V_{CU}) during charging under normal conditions and the state is retained for the overcharge detection delay time (t_{CU}) or longer, CO becomes "H". This state is called overcharge. Attaching FET to the CO pin provides charge control and a second protection.

In the S-8264A/C Series, if the voltage of all the batteries decreases below the total of the overcharge detection voltage (V_{CU}) and the overcharge hysteresis voltage (V_{HC}) and the state is retained for the overcharge release delay time (t_{CL}) or longer, CO becomes "L".

In the S-8264B Series, if the voltage of all the batteries decreases below the total of the overcharge detection voltage (V_{CU}) and the overcharge hysteresis voltage (V_{HC}) and the state is retained for the overcharge release delay time (t_{CL}) or longer, the overcharge status is released; however, CO stays at "H". When the CTL pin is switched from "L" to "H", CO becomes "L".

2. Overcharge Timer Reset

When an overcharge release noise that forces the voltage of the battery temporarily below the overcharge detection voltage (V_{CU}) is input during the overcharge detection delay time (t_{CU}) from when V_{CU} is exceeded to when charging is stopped, t_{CU} is continuously counted if the time the overcharge release noise persists is shorter than the overcharge timer reset delay time (t_{TR}). Under the same conditions, if the time the overcharge release noise persists is t_{TR} or longer, counting of t_{CU} is reset once. After that, when V_{CU} has been exceeded, counting t_{CU} resumes.

3. CTL Pin

The S-8264A/B/C Series has a control pin. The CTL pin is used to control the output voltage of the CO pin. In the S-8264A/C Series, the CTL pin takes precedence over the overcharge detection circuit.

In the S-8264B Series, when the CTL pin is switched from "L" to "H", a reset signal is output to the overcharge detection latch and CO becomes "L".

CTI Din		CO Pin	
	S-8264A Series	S-8264B Series	S-8264C Series
"Н"	Normal state ^{*1}	Without latch	Normal state ^{*1}
Open	"H"	Normal state ^{*1}	Normal state ^{*1}
"L"	"H"	Normal state ^{*1}	"H"
"L" → "H"	-	Latch reset ^{*2}	-
"H" → "L"	_	-	_

Table 12 Control via CTL Pin

*1. The state is controlled by the overcharge detection circuit.

*2. Latch reset becomes effective when the voltages of all the batteries are lower than the total of the overcharge detection voltage (V_{CU}) and the overcharge hysteresis voltage (V_{HC}) and the overcharge release delay time (t_{CL}) has elapsed.



*1. The reverse voltage "H" to "L" or "L" to "H" of CTL pin is VDD pin voltage - 2.8 V (Typ.), does not have the hysteresis.

Figure 8 Internal Equivalent Circuit of CTL Pin

- Caution 1. In the S-8264A/B Series, since the CTL pin implements high resistance of 8 M Ω to 12 M Ω for pull down, be careful of external noise application. If an external noise is applied, CO may become "H". Perform thorough evaluation using the actual application.
 - 2. In the S-8264B Series, when the CTL pin is open or "L", CO latches "H". When the VDD pin voltage is decreased to the UVLO voltage of 2 V (Typ.) or lower, the latch is reset.

4. Test Mode

In the S-8264A/B/C Series, the overcharge detection delay time (t_{CU}) can be shortened by entering the test mode. The test mode can be set by retaining the VDD pin voltage 8.5 V or more higher than the SENSE pin voltage for at least 80 ms (V1 = V2 = V3 = V4 = 3.5 V, Ta = 25°C). The status is retained by the internal latch and the test mode is retained even if the VDD pin voltage is decreased to the same voltage as that of the SENSE pin.

When CO becomes "H" when the delay time has elapsed after overcharge detection, the latch for retaining the test mode is reset and the S-8264A/B Series exits from the test mode.



*1. In the product $t_{CU} = 4$ s Typ. during normal mode, $t_{CU} = 64$ ms Typ. In the product $t_{CU} = 2$ s Typ. during normal mode, $t_{CU} = 32$ ms Typ. In the product $t_{CU} = 5.65$ s Typ. during normal mode, $t_{CU} = 88$ ms Typ.

Figure 9

- Caution 1. When the VDD pin voltage is decreased to lower than the UVLO voltage of 2 V (Typ.), the S-8264A/B/C Series returns to the normal mode.
 - 2. Set the test mode when no batteries are overcharged.
 - 3. The overcharge release delay time (t_{CL}) is not shortened in the test mode.
 - 4. The overcharge timer reset delay time (t_{TR}) is not shortened in the test mode.

Timing Charts

1. Overcharge Detection Operation

(1) S-8264A/C Series

(2) S-8264B Series



Figure 10



Figure 11

2. Overcharge Timer Reset Operation



Figure 12

Battery Protection IC Connection Example

(1) 4-serial cell



Figure 13

*1. Refer to Table 12 for setting on external input.

Table 13 Constants for External Components

No.	Part	Min.	Тур.	Max.	Unit
1	R1 to R4	0.1	1	10	kΩ
2	C1 to C4, C _{VDD}	0.01	0.1	1	μF
3	R _{VDD}	50	100	500	Ω
4	R _{CTL}	0	100	500	Ω

Caution 1. The above constants are subject to change without prior notice.

- 2. It has not been confirmed whether the operation is normal or not in circuits other than the above example of connection. In addition, the example of connection shown above and the constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.
- 3. Set the same constants to R1 to R4 and to C1 to C4 and C_{VDD} .
- 4. Set R_{VDD}, C1 to C4, and C_{VDD} so that the condition (R_{VDD}) × (C1 to C4, C_{VDD}) \ge 5 × 10⁻⁶ is satisfied.
- 5. Set R1 to R4, C1 to C4, and C_{VDD} so that the condition (R1 to R4) × (C1 to C4, C_{VDD}) \ge 1 × 10⁻⁴ is satisfied.
- 6. Since "H" may be output at CO transiently when the battery is being connected, connect the positive terminal of BAT1 last in order to prevent the three terminal protection fuse from cutoff.

(2) 3-serial cell



Figure 14

*1. Refer to Table 12 for setting on external input.

 Table 14 Constants for External Components

No.	Part	Min.	Тур.	Max.	Unit
1	R1 to R3	0.1	1	10	kΩ
2	C1 to C3, C _{VDD}	0.01	0.1	1	μF
3	R _{VDD}	50	100	500	Ω
4	R _{CTL}	0	100	500	Ω

Caution 1. The above constants are subject to change without prior notice.

2. It has not been confirmed whether the operation is normal or not in circuits other than the above example of connection. In addition, the example of connection shown above and the constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

- 3. Set the same constants to R1 to R3 and to C1 to C3 and C_{VDD} .
- 4. Set R_{VDD}, C1 to C3, and C_{VDD} so that the condition (R_{VDD}) × (C1 to C3, C_{VDD}) \ge 5 × 10⁻⁶ is satisfied.
- 5. Set R1 to R3, C1 to C3, and C_{VDD} so that the condition (R1 to R3) × (C1 to C3, C_{VDD}) \ge 1 × 10⁻⁴ is satisfied.
- 6. Since "H" may be output at CO transiently when the battery is being connected, connect the positive terminal of BAT1 last in order to prevent the three terminal protection fuse from cutoff.

(3) 2-serial cell



Figure 15

*1. Refer to Table 12 for setting on external input.

 Table 15 Constants for External Components

No.	Part	Min.	Тур.	Max.	Unit
1	R1 and R2	0.1	1	10	kΩ
2	C1 and C2, C _{VDD}	0.01	0.1	1	μF
3	R _{VDD}	50	100	500	Ω
4	R _{CTL}	0	100	500	Ω

Caution 1. The above constants are subject to change without prior notice.

2. It has not been confirmed whether the operation is normal or not in circuits other than the above example of connection. In addition, the example of connection shown above and the constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

- 3. Set the same constants to R1 to R3 and to C1 to C3 and $C_{\text{VDD}}.$
- 4. Set R_{VDD} , C1 to C3, and C_{VDD} so that the condition (R_{VDD}) × (C1 to C3, C_{VDD}) \ge 5 × 10⁻⁶ is satisfied.
- 5. Set R1 to R3, C1 to C3, and C_{VDD} so that the condition (R1 to R3) × (C1 to C3, C_{VDD}) \ge 1 × 10⁻⁴ is satisfied.
- 6. Since "H" may be output at CO transiently when the battery is being connected, connect the positive terminal of BAT1 last in order to prevent the three terminal protection fuse from cutoff.

Precautions

- Do not connect batteries charged with $V_{CU} + V_{HC}$ or more. If the connected batteries include a battery charged with $V_{CU} + V_{HC}$ or more, "H" may be output at CO after all pins are connected.
- In some application circuits, even if an overcharged battery is not included, the order of connecting batteries may be restricted to prevent transient output of CO detection pulses when the batteries are connected. Perform thorough evaluation with the actual application circuit.
- In the S-8264B Series, "H" may be output at CO after all the pins are connected. In this case, set the CTL pin from "L" to "H".
- Before the battery connection, short-circuit the battery side pins R_{VDD} and R1, shown in the figure in "■ Battery Protection IC Connection Example".
- The application conditions for the input voltage, output voltage, and load current should not exceed the package power dissipation.
- Do not apply to this IC an electrostatic discharge that exceeds the performance ratings of the built-in electrostatic protection circuit.
- SII claims no responsibility for any disputes arising out of or in connection with any infringement of patents owned by a third party by products including this IC.

Example of Application Circuit

1. Overheat Protection via PTC (S-8264A Series)



Figure 16

- Cautions 1. The above connection example will not guarantee successful operation. Perform thorough evaluation using the actual application.
 - 2. A pull-down resistor is included in the CTL pin. To perform overheat protection via the PTC in the S-8264A Series, connect the PTC before connecting batteries.
 - 3. When the power fluctuation is large, connect the power supply of the PTC to the VDD pin of the S-8264A Series.
 - 4. Since "H" may be output at CO transiently when the battery is being connected, connect the positive terminal of BAT1 last in order to prevent the three terminal protection fuse from cutoff.

[For SC PROTECTOR, contact]

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■ Characteristics (Typical Data)

1. Detection Voltage vs. Temperature



2. Current Consumption vs. Temperature

(1) Current Consumption during Normal Operation vs. Temperature



3. Delay Time vs. Temperature

(1) Overcharge Detection Delay Time vs. Temperature





(2) Current Consumption during Overdischarge vs. Temperature $$V_{\text{DD}}$$ = 9.2 V





(2) Overcharge Release Delay Time vs. Temperature $$V_{\text{DD}}$$ = 14 V



5. CTL Pin vs. Temperature





(2) CTL Pin Input Resistance vs. Temperature



Marking Specifications

(1) SNT-8A



(1) (2) to (4) (5), (6) (7) to (11) Blank Product code (Refer to **Product name vs. Product code**) Blank Lot number

Product name vs. Product code

(a) S-8264A Series

Product name	Product code		
Troduct hame	(2)	(3)	(4)
S-8264AAA-I8T1x	Q	5	А
S-8264AAB-I8T1x	Q	5	В
S-8264AAC-I8T1x	Q	5	С
S-8264AAD-I8T1x	Q	5	D
S-8264AAE-I8T1x	Q	5	Е
S-8264AAF-I8T1x	Q	5	F
S-8264AAG-I8T1x	Q	5	G
S-8264AAH-I8T1x	Q	5	Н
S-8264AAI-I8T1x	Q	5	Ι
S-8264AAJ-I8T1x	Q	5	J
S-8264AAK-I8T1x	Q	5	К

(b) S-8264B Series

Product name	Product code		
Troduct name	(2)	(3)	(4)
S-8264BAA-I8T1x	Q	6	А
S-8264BAB-I8T1x	Q	6	В

(c) S-8264C Series

Product name	Product code		
T Toudet hame	(2)	(3)	(4)
S-8264CAA-I8T1U	Q	7	Α
S-8264CAB-I8T1U	Q	7	В

(2) 8-Pin TSSOP



Product name: S8264 (Fixed) Function code Lot number

Product name vs. Function code

(a) S-8264A Series

Product name	Function code		
i foddet fiame	(6)	(7)	(8)
S-8264AAA-T8T1x	А	А	Α
S-8264AAB-T8T1x	Α	А	В

Remark 1. x: G or U

2. Please select products of environmental code = U for Sn 100%, halogen-free products.

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No. PH008-A-P-SD-2.0

TITLE	SNT-8A-A-PKG Dimensions		
No.	PH008-A-P-SD-2.0		
SCALE			
UNIT	mm		
	aika Inatrumanta Ina		
Seiko instruments inc.			



Seiko Instruments Inc.





Seiko Instruments Inc.

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No. FT008-A-P-SD-1.1

TITLE	TSSOP8-E-PKG Dimensions		
No.	FT008-A-P-SD-1.1		
SCALE			
UNIT	mm		
Seiko Instruments Inc.			









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